

DOCKET: CU-3859

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Erich Gornick et al

Serial No.: 10/502,503

Group Art Unit:

Filed: July 23, 2004

Examiner:

For: METHOD AND DEVICE FOR OPTICALLY TESTING SEMICONDUCTOR
ELEMENTS

THE COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, VA 22313-1450

**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT WITHIN THREE
MONTHS OF FILING OR BEFORE MAILING OF FIRST OFFICE ACTION**

The information disclosure statement submitted herewith is being filed within three months of the filing date of the application or date of entry into the national stage of an international application or before the mailing date of the first Office Action on the merits, whichever event occurs last. 37 CFR 1.97(b).

Date: October 13, 2004



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INFORMATION DISCLOSURE STATEMENT

Applicants submit herewith patents, publications or other information of which the applicants are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose under 37 CFR 1.56.

The filing of this information disclosure statement shall not be construed as a representation that a search has been made (37 CFR 1.97(g)), an admission that the information cited is, or is considered to be, material to patentability or that no other material information exists.

The filing of this information disclosure statement shall not be construed as an admission against interest in any manner. Notice of January 9, 1992, 1135 O.G. 1325, at 25.

The references submitted herein are listed on PTO-1449 form (modified) enclosed herewith. A copy of each reference listed is being furnished except any duplicate or cumulative patents or publications specified otherwise. Also, if the present application was filed after June 30, 2003, copies of US patents or published applications are not submitted in accordance with the USPTO Rule changes.

A translation of any foreign language reference, if any, is indicated in PTO-1449 form and being submitted herein if it is readily available. Otherwise it should be construed that such translation is not readily available.

Additional comments, if any, on the relevance of each reference listed are provided as follows:

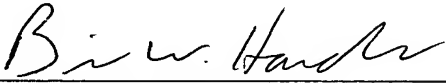
Also submitted herein is a copy of the International Search Report which satisfies the requirement for a translation or concise explanation of any non-English reference cited therein, as provided in MPEP §609 A(3).

The Statement is made on the basis of the information:

<u> </u>	supplied by the inventor(s);
<u> X </u>	supplied by an individual associated with the filing and prosecution
<u> </u>	of this application (37 CFR 1.56(c)); or
	in the attorney's file.

Respectfully submitted,

Date: October 13, 2004



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Form PTO-1449 (Modified)

FORM PTO-1449	ATTY. DOCKET NO.	SERIAL NO.
	CU-3859	10/502,503
	APPLICANT	
	Erich Gornick et al	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	FILING DATE	GROUP
	July 23, 2004	
(37 CFR 1.98(b))		

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
	US	5 4 1 4 5 1 3	05/09/1995				
	US	4 9 5 7 3 6 7	09/18/1990				
	US	4 8 4 1 1 5 0	06/20/1989				
	US	5 2 2 9 3 0 3	07/20/1993				
	US	5 7 7 3 3 1 6	06/30/1998				
	US	6 1 8 1 4 1 6	01/30/2001				
	US	6 2 2 2 1 8 7	04/24/2001				
	US	4 6 8 2 6 0 5	07/28/1987				
	US	4 8 1 8 1 1 0	04/40/1989				

FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLA SS	SUB- CLASS	TRANSLATION YES I NO
	1	0 0 4 7 1 3 6	04/19/2001	German			
	WO	0 0 5 7 1 5 9	09/28/2000	PCT			
	1	9 8 4 0 7 2 5	03/18/1999	German			
	1	9 5 1 6 8 4 2	11/30/1995	German			
	EP	0 6 1 8 4 5 5	05/10/1994	EPO			
	WO	9 7 1 3 3 5 8	04/10/1997	PCT			
	GB	2 2 1 7 0 1 1	10/18/1989	United Kingdom			

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EXAMINER	DATE CONSIDERED	

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(37 CFR 1.98(b))	FILING DATE	GROUP
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